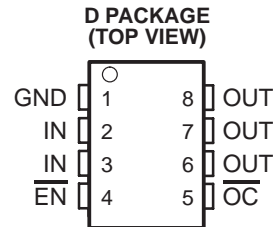


TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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- Qualified for Automotive Applications
- 33-mΩ (5-V Input) High-Side MOSFET Switch
- Short-Circuit and Thermal Protection
- Overcurrent Logic Output
- Operating Range . . . 2.7 V to 5.5 V
- Logic-Level Enable Input
- Typical Rise Time . . . 6.1 ms
- Undervoltage Lockout
- Maximum Standby Supply Current . . . 10 μA
- No Drain-Source Back-Gate Diode
- Available in 8-Pin SOIC Package
- Ambient Temperature Range . . . –40°C to 85°C
- ESD Protection . . . 2-kV Human-Body Model, 200-V Machine Model
- UL Listed – File No. E169910



description

The TPS202x family of power-distribution switches is intended for applications where heavy capacitive loads and short circuits are likely to be encountered. These devices are 50-mΩ N-channel MOSFET high-side power switches. The switch is controlled by a logic enable compatible with 5-V logic and 3-V logic. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V.

When the output load exceeds the current-limit threshold or a short is present, the TPS202x limits the output current to a safe level by switching into a constant-current mode, pulling the overcurrent (OC) logic output low. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures the switch remains off until valid input voltage is present.

The TPS202x devices differ only in short-circuit current threshold. The TPS2021 limits at 0.9-A load, the TPS2022 limits at 1.5-A load, and the TPS2024 limits at 3-A load (see Available Options). The TPS202x is available in an 8-pin small-outline integrated circuit (SOIC) package and operates over a junction temperature range of –40°C to 125°C.

GENERAL SWITCH CATALOG			
33 mΩ, single TPS201xA 0.2 A – 2 A TPS202x 0.2 A – 2 A TPS203x 0.2 A – 2 A	80 mΩ, dual TPS2042 500 mA TPS2052 500 mA TPS2046 250 mA TPS2056 250 mA	80 mΩ, triple TPS2043 500 mA TPS2053 500 mA TPS2047 250 mA TPS2057 250 mA	80 mΩ, quad TPS2044 500 mA TPS2054 500 mA TPS2048 250 mA TPS2058 250 mA
80 mΩ, single TPS2014 600 mA TPS2015 1 A TPS2041 500 mA TPS2051 500 mA TPS2045 250 mA TPS2055 250 mA	260 mΩ TPS2100/1 IN1 500 mA IN2 10 mA TPS2102/3/4/5 IN1 500 mA IN2 100 mA		



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TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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AVAILABLE OPTIONS[†]

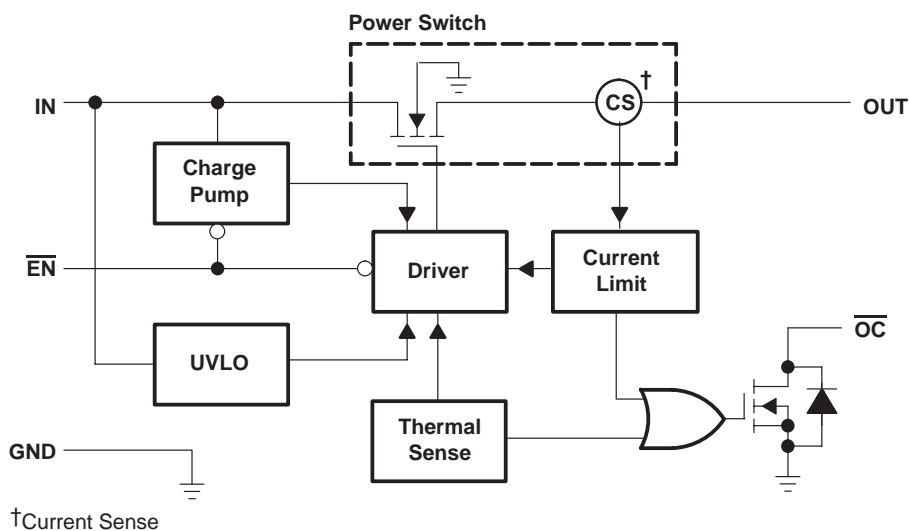
T _A	ENABLE	RECOMMENDED MAXIMUM CONTINUOUS LOAD CURRENT (A)	TYPICAL SHORT-CIRCUIT CURRENT LIMIT AT 25°C (A)	PACKAGED DEVICES [‡]
				SMALL OUTLINE (D) [§]
-40°C to 85°C	Active low	0.6	0.9	TPS2021IDRQ1
		1	1.5	TPS2022DRQ1
		2	3	TPS2024IDRQ1

[†] For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at <http://www.ti.com>.

[‡] Package drawings, thermal data, and symbolization are available at <http://www.ti.com/packaging>.

[§] The D package is taped and reeled as indicated by the R suffix to device type (e.g., TPS2021IDRQ1).

functional block diagram



Terminal Functions

TERMINAL		I/O	DESCRIPTION
NAME	NO.		
$\overline{\text{EN}}$	4	I	Enable input. Logic low turns on power switch.
GND	1	I	Ground
IN	2, 3	I	Input voltage
$\overline{\text{OC}}$	5	O	Overcurrent. Logic output active low.
OUT	6, 7, 8	O	Power-switch output

detailed description

power switch

The power switch is an N-channel MOSFET with a maximum on-state resistance of 50 m Ω ($V_{I(IN)} = 5$ V). Configured as a high-side switch, the power switch prevents current flow from OUT to IN and IN to OUT when disabled.

charge pump

An internal charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires little supply current.

driver

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage. The rise and fall times are typically in the 2-ms to 9-ms range.

enable (\overline{EN})

The logic enable disables the power switch, the bias for the charge pump, driver, and other circuitry to reduce the supply current to less than 10 μ A when a logic high is present on \overline{EN} . A logic zero input on \overline{EN} restores bias to the drive and control circuits and turns the power on. \overline{EN} is compatible with both TTL and CMOS logic levels.

overcurrent (\overline{OC})

The \overline{OC} open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output remains asserted until the overcurrent or overtemperature condition is removed.

current sense

A sense FET monitors the current supplied to the load. The sense FET measures current more efficiently than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver, in turn, reduces the gate voltage and drives the power FET into its saturation region, which switches the output into a constant current mode and holds the current constant while varying the voltage on the load.

thermal sense

An internal thermal-sense circuit shuts off the power switch when the junction temperature rises to approximately 140°C. Hysteresis is built into the thermal sense circuit. After the device has cooled approximately 20°C, the switch turns back on. The switch continues to cycle off and on until the fault is removed.

undervoltage lockout

A voltage sense circuit monitors the input voltage. When the input voltage is below approximately 2 V, a control signal turns off the power switch.

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input voltage range, $V_{I(IN)}$ (see Note 1)	-0.3 V to 6 V
Output voltage range, $V_{O(OUT)}$ (see Note 1)	-0.3 V to $V_{I(IN)} + 0.3$ V
Input voltage range, $V_{I(EN)}$	-0.3 V to 6 V
Continuous output current, $I_{O(OUT)}$	internally limited
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T_J	-40°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Electrostatic discharge (ESD) protection: Human-Body Model (HBM)	2 kV
Machine Model (MM)	200V
Charged-Device Model (CDM)	750 V

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW

recommended operating conditions

		MIN	MAX	UNIT
Input voltage	$V_{I(IN)}$	2.7	5.5	V
	$V_{I(EN)}$	0	5.5	
Continuous output current, I_O	TPS2021	0	0.6	A
	TPS2022	0	1	
	TPS2024	0	2	
Operating virtual junction temperature, T_J		-40	125	°C



TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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electrical characteristics over recommended operating junction temperature range, $V_{I(IN)} = 5.5\text{ V}$, $I_O = \text{rated current}$, $\overline{EN} = 0\text{ V}$ (unless otherwise noted)

power switch

PARAMETER		TEST CONDITIONS†	T_J	MIN	TYP	MAX	UNIT
$r_{DS(on)}$	Static drain-source on-state resistance	$V_{I(IN)} = 5\text{ V}$, $I_O = 1.8\text{ A}$	25°C		33	43.5	mΩ
			85°C		38	57.5	
			125°C		44	62.5	
		$V_{I(IN)} = 3.3\text{ V}$, $I_O = 1.8\text{ A}$	25°C		37	48.5	
			85°C		43	68.5	
			125°C		51	87	
		$V_{I(IN)} = 5\text{ V}$, $I_O = 1\text{ A}$	25°C		30	43.5	
			125°C		43	62.5	
		$V_{I(IN)} = 3.3\text{ V}$, $I_O = 1\text{ A}$	25°C		31	48.5	
			125°C		48	87	
		$V_{I(IN)} = 5\text{ V}$, $I_O = 0.18\text{ A}$	25°C		30	34	
			85°C		35	41	
			125°C		39	47	
		$V_{I(IN)} = 3.3\text{ V}$, $I_O = 0.18\text{ A}$	25°C		33	37	
			85°C		39	46	
			125°C		44	56	
$V_{I(IN)} = 5\text{ V}$, $I_O = 0.6\text{ A}$, TPS2021	25°C		33	36			
	125°C		44	48			
$V_{I(IN)} = 3.3\text{ V}$, $I_O = 0.6\text{ A}$, TPS2021	25°C		37	40			
	125°C		51	59			
t_r	Rise time, output	$V_{I(IN)} = 5.5\text{ V}$, $C_L = 1\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$	25°C		6.1		ms
		$V_{I(IN)} = 2.7\text{ V}$, $C_L = 1\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$	25°C		8.6		
t_f	Fall time, output	$V_{I(IN)} = 5.5\text{ V}$, $C_L = 1\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$	25°C		3.4		ms
		$V_{I(IN)} = 2.7\text{ V}$, $C_L = 1\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$	25°C		3		

† Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

enable input (\overline{EN})

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
V_{IH}	High-level input voltage	$2.7\text{ V} \leq V_{I(IN)} \leq 5.5\text{ V}$	2		V
V_{IL}	Low-level input voltage	$4.5\text{ V} \leq V_{I(IN)} \leq 5.5\text{ V}$		0.8	V
		$2.7\text{ V} \leq V_{I(IN)} \leq 4.5\text{ V}$		0.5	
I_I	Input current	$\overline{EN} = 0\text{ V}$ or $\overline{EN} = V_{I(IN)}$	-0.5	0.5	μA
t_{on}	Turnon time	$C_L = 100\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$		20	ms
t_{off}	Turnoff time	$C_L = 100\text{ }\mu\text{F}$, $R_L = 10\text{ }\Omega$		40	ms

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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electrical characteristics over recommended operating junction temperature range, $V_{I(IN)} = 5.5\text{ V}$, $I_O = \text{rated current}$, $\overline{EN} = 0\text{ V}$ (unless otherwise noted) (continued)

current limit

PARAMETER		TEST CONDITIONS†	MIN	TYP	MAX	UNIT	
I_{OS}	Short-circuit output current	$T_J = 25^\circ\text{C}$, $V_I = 5.5\text{ V}$, OUT connected to GND, Device enable into short circuit	TPS2021	0.66	0.9	1.1	A
			TPS2022	1.1	1.5	1.8	
			TPS2024	2	3	4.2	

† Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

supply current

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
Supply current, low-level output	No load on OUT	$\overline{EN} = V_{I(IN)}$	$T_J = 25^\circ\text{C}$	0.3	1	μA	
			$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$		10		
Supply current, high-level output	No load on OUT	$\overline{EN} = 0\text{ V}$	$T_J = 25^\circ\text{C}$	58	75	μA	
			$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	75	100		
Leakage current	OUT connected to ground	$\overline{EN} = V_{I(IN)}$	$-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	10		μA	

undervoltage lockout

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Low-level input voltage		2		2.5	V
Hysteresis	$T_J = 25^\circ\text{C}$		100		mV

overcurrent (\overline{OC})

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
Output low voltage	$I_O = 10\text{ mA}$, $V_{OL(\overline{OC})}$		0.4	V
Off-state current†	$V_O = 5\text{ V}$, $V_O = 3.3\text{ V}$		1	μA

† Specified by design

PARAMETER MEASUREMENT INFORMATION

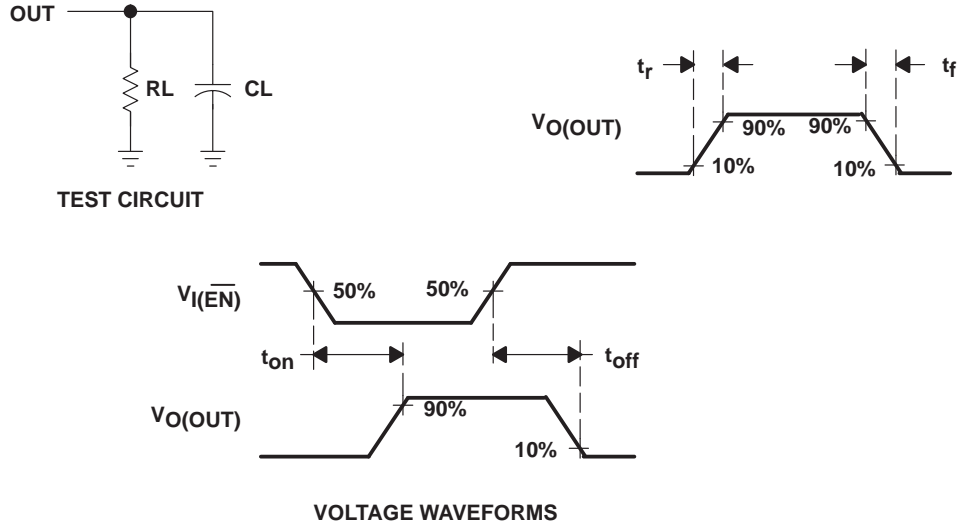


Figure 1. Test Circuit and Voltage Waveforms

Table of Timing Diagrams

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TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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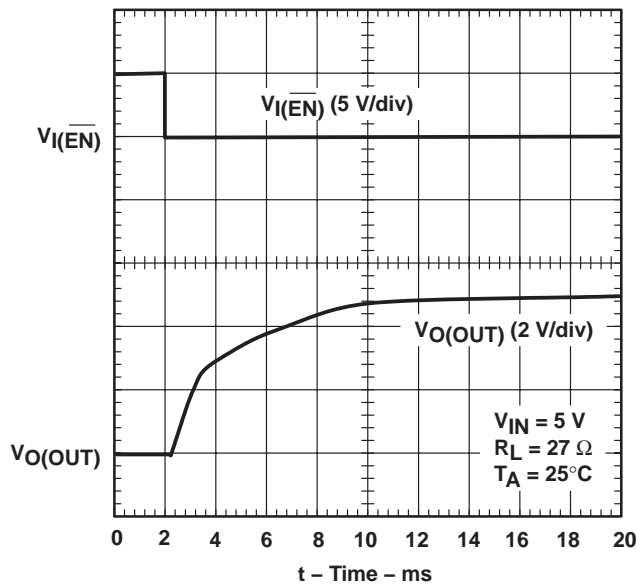


Figure 2. Turnon Delay and Rise Time

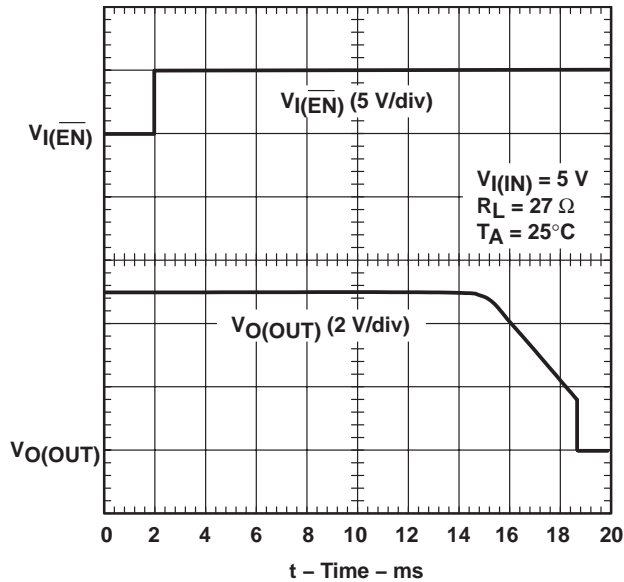


Figure 3. Turnoff Delay and Fall Time

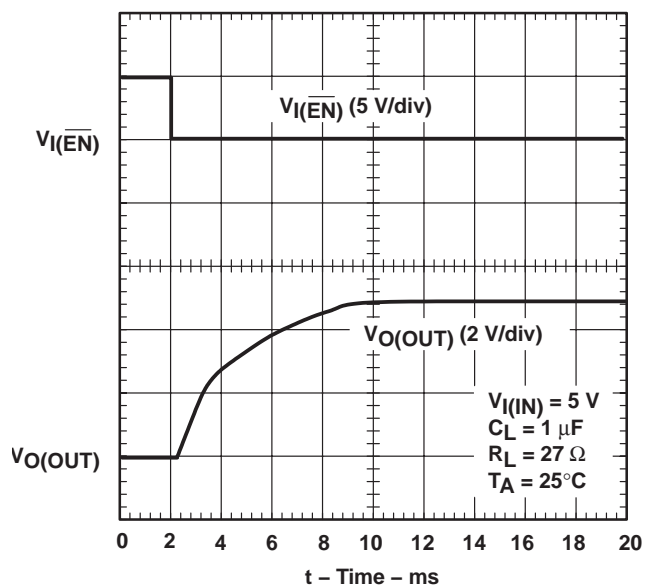


Figure 4. Turnon Delay and Rise Time
With 1- μ F Load

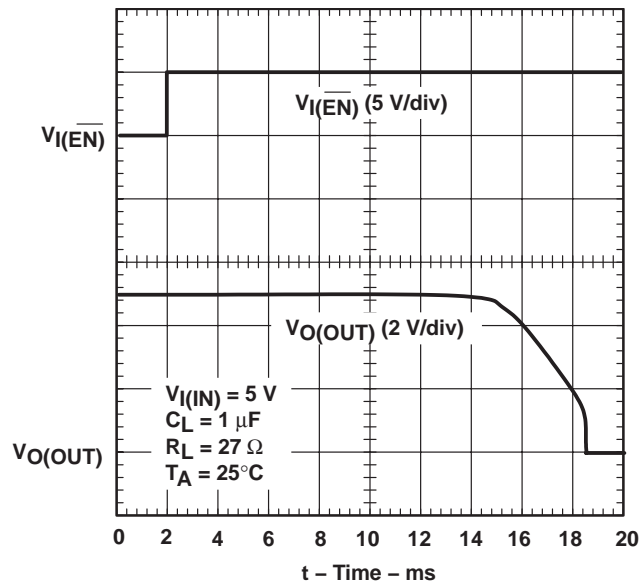


Figure 5. Turnoff Delay and Fall Time
With 1- μ F Load

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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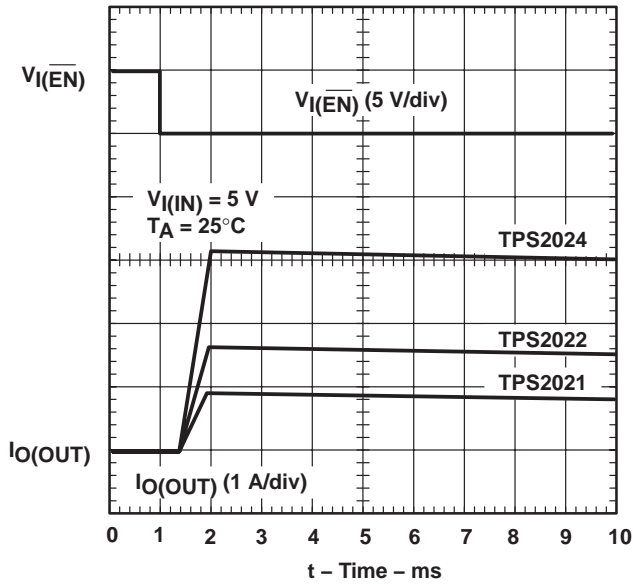


Figure 6. Device Enabled Into Short

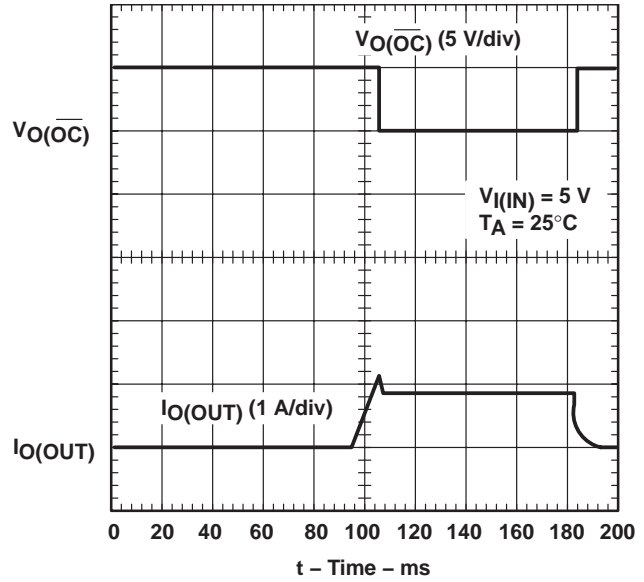


Figure 7. TPS2021 Ramped Load on Enabled Device

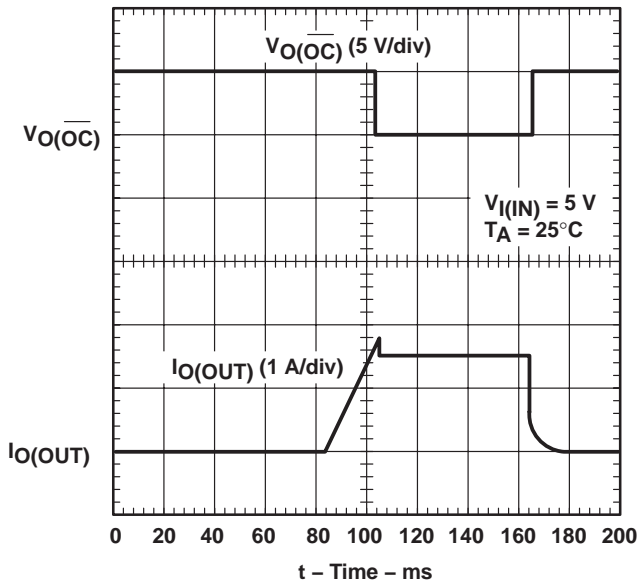


Figure 8. TPS2022 Ramped Load on Enabled Device

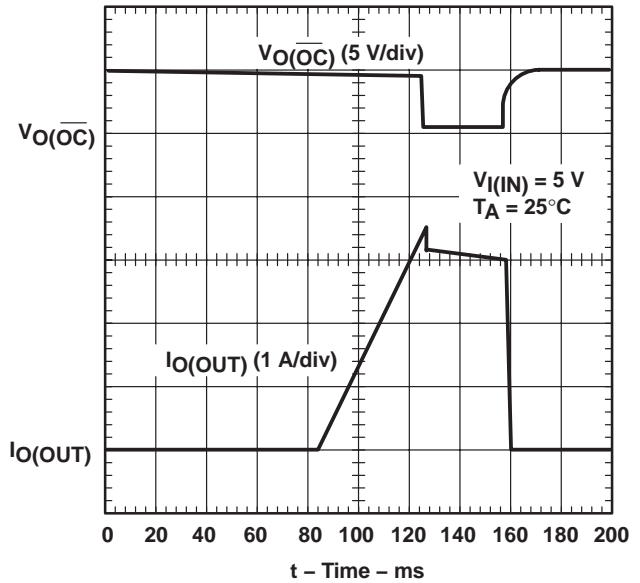


Figure 9. TPS2024 Ramped Load on Enabled Device

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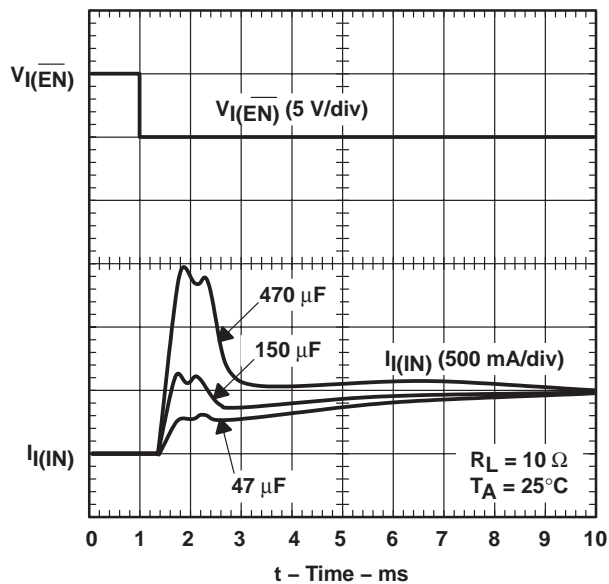


Figure 10. TPS2024 Inrush Current

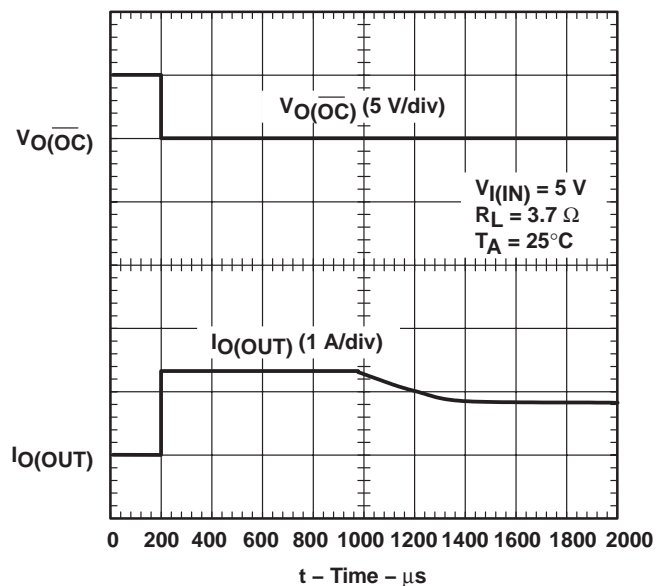


Figure 11. 3.7-Ω Load Connected to an Enabled TPS2021 Device

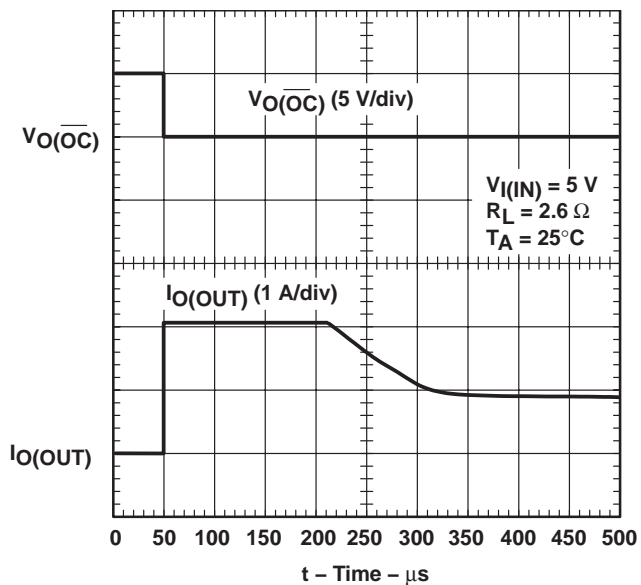


Figure 12. 2.6-Ω Load Connected to an Enabled TPS2021 Device

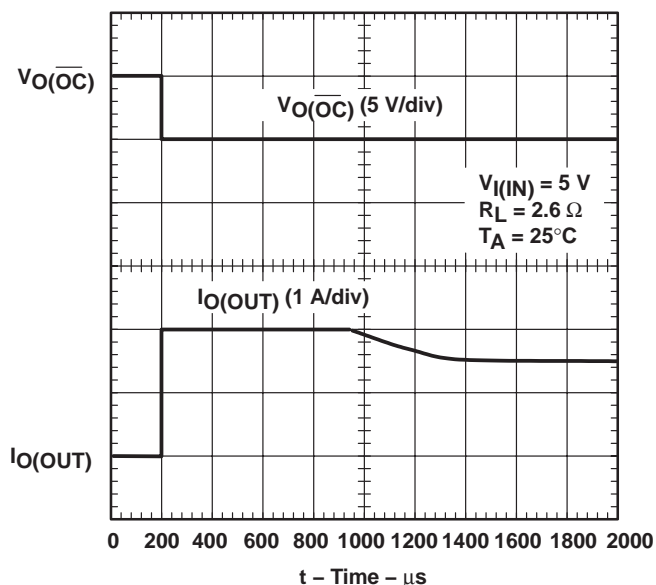


Figure 13. 2.6-Ω Load Connected to an Enabled TPS2022 Device

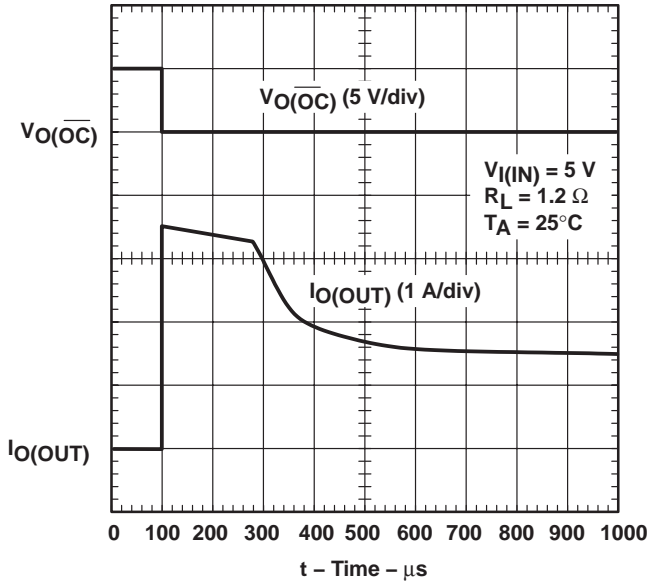


Figure 14. 1.2- Ω Load Connected to an Enabled TPS2022 Device

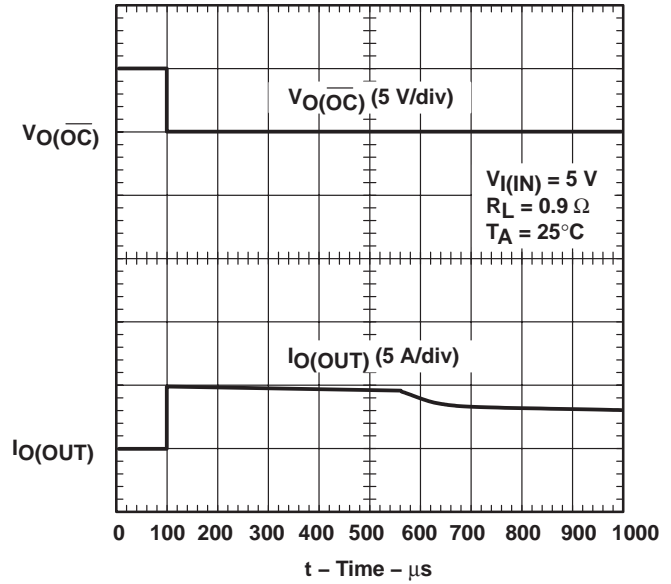


Figure 15. 0.9- Ω Load Connected to an Enabled TPS2024 Device

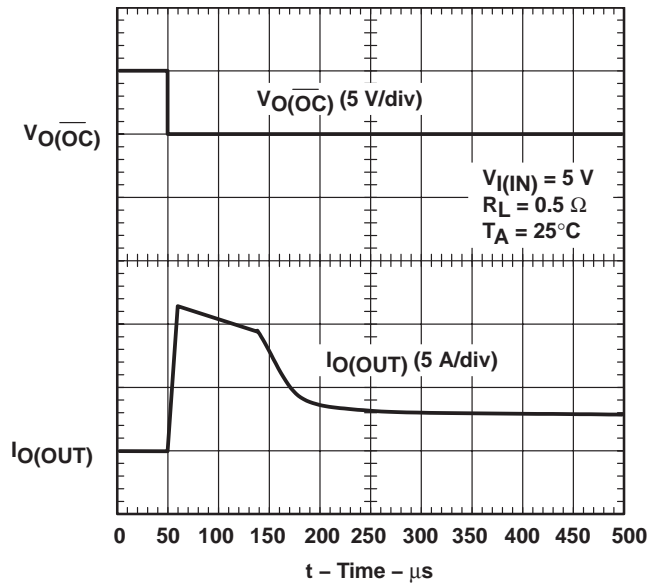


Figure 16. 0.5- Ω Load Connected to an Enabled TPS2024 Device

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TYPICAL CHARACTERISTICS

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	Supply current (disabled)	vs Junction temperature	22
	Supply current (enabled)	vs Input voltage	23
	Supply current (disabled)	vs Input voltage	24
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		vs Junction temperature	26
$r_{DS(on)}$	Static drain-source on-state resistance	vs Input voltage	27
		vs Junction temperature	28
		vs Input voltage	29
		vs Junction temperature	30
V_{I3}	Undervoltage lockout		31

TURNON DELAY TIME
vs
OUTPUT VOLTAGE

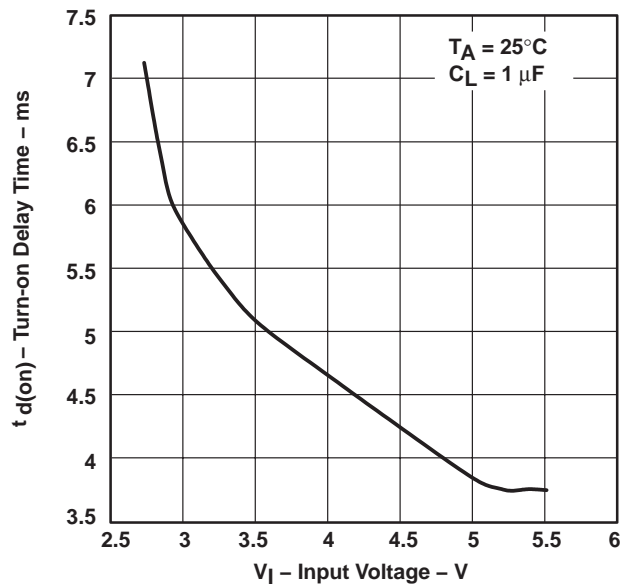


Figure 17

TURNOFF DELAY TIME
vs
INPUT VOLTAGE

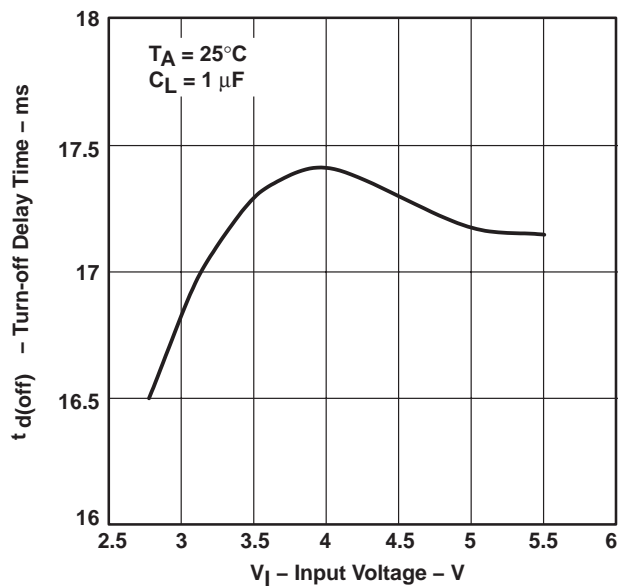


Figure 18

**RISE TIME
 VS
 LOAD CURRENT**

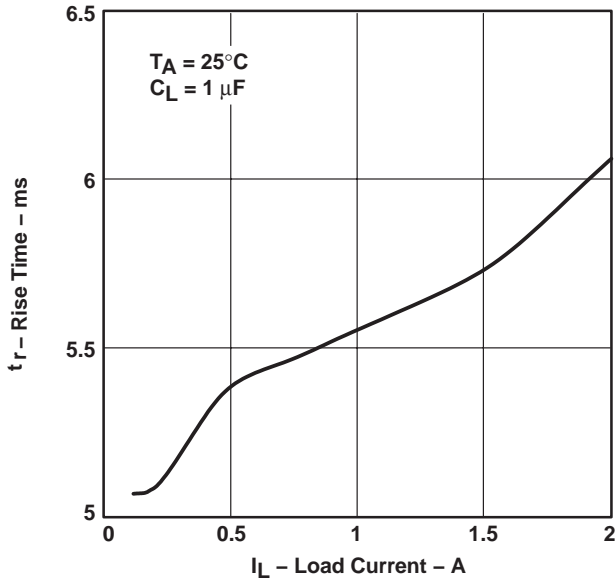


Figure 19

**FALL TIME
 VS
 LOAD CURRENT**

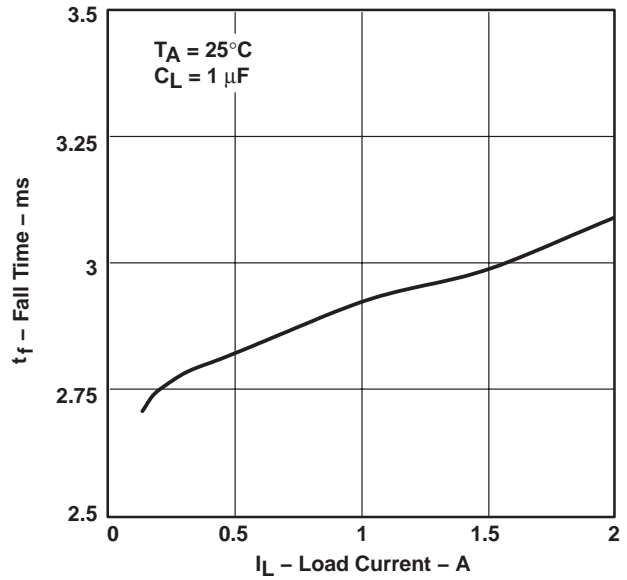


Figure 20

**SUPPLY CURRENT (ENABLED)
 VS
 JUNCTION TEMPERATURE**

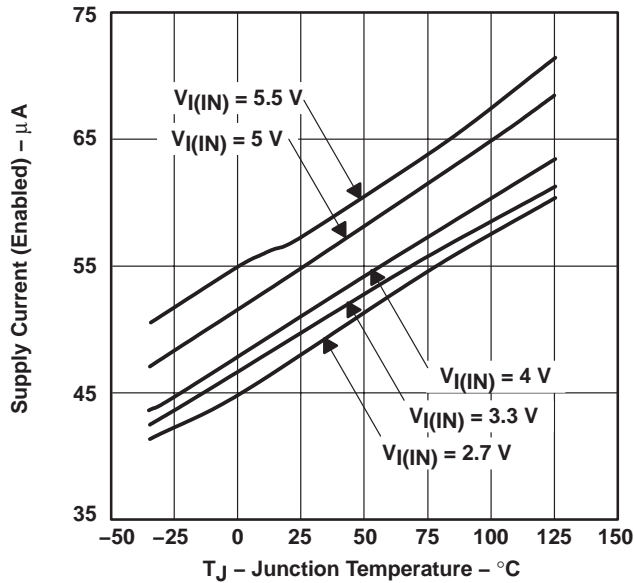


Figure 21

**SUPPLY CURRENT (DISABLED)
 VS
 JUNCTION TEMPERATURE**

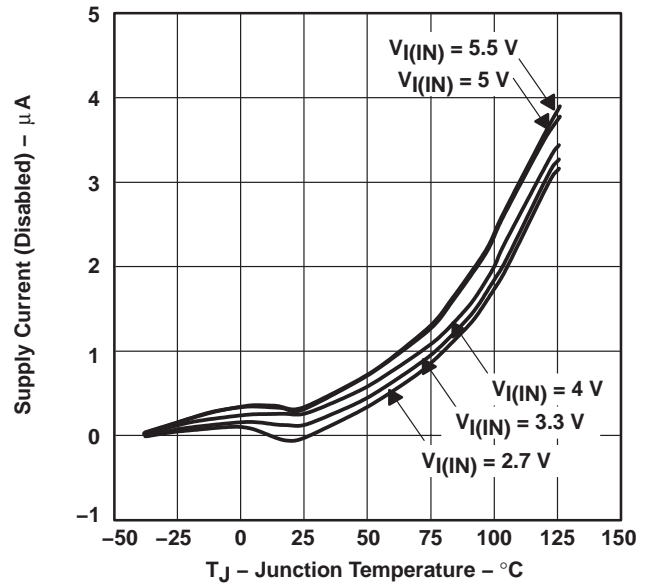


Figure 22

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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**SUPPLY CURRENT (ENABLED)
vs
INPUT VOLTAGE**

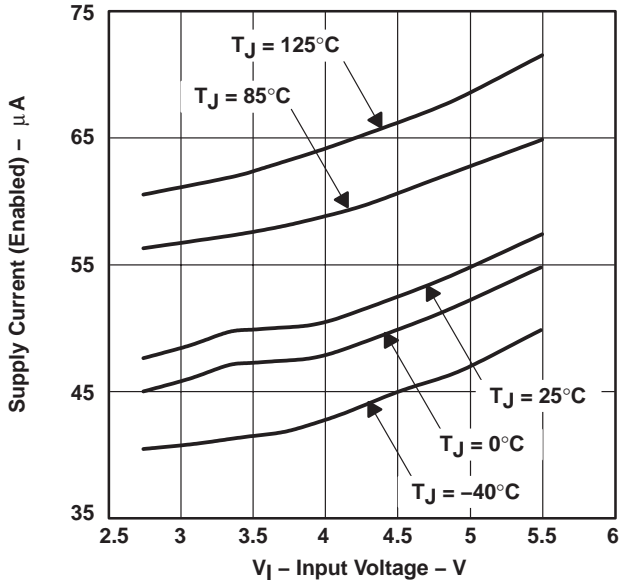


Figure 23

**SUPPLY CURRENT (DISABLED)
vs
INPUT VOLTAGE**

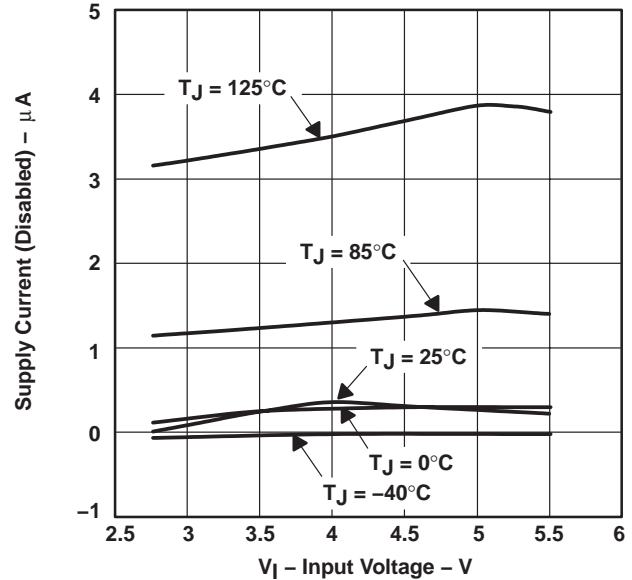


Figure 24

**SHORT-CIRCUIT CURRENT LIMIT
vs
INPUT VOLTAGE**

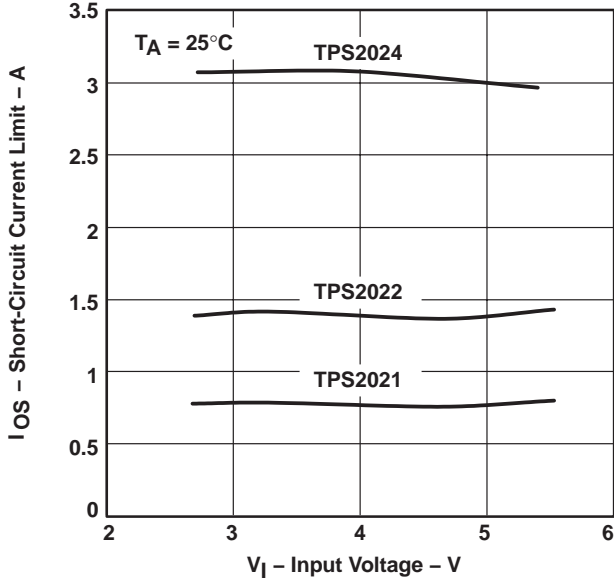


Figure 25

**SHORT-CIRCUIT CURRENT LIMIT
vs
JUNCTION TEMPERATURE**

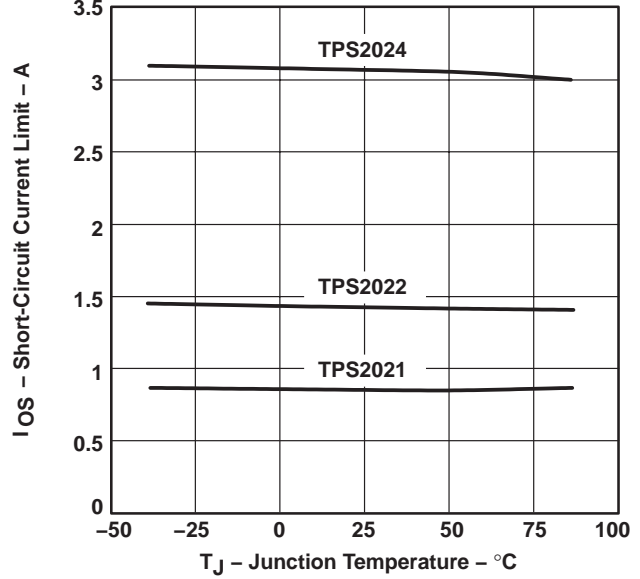


Figure 26

STATIC DRAIN-SOURCE ON-STATE RESISTANCE
vs
INPUT VOLTAGE

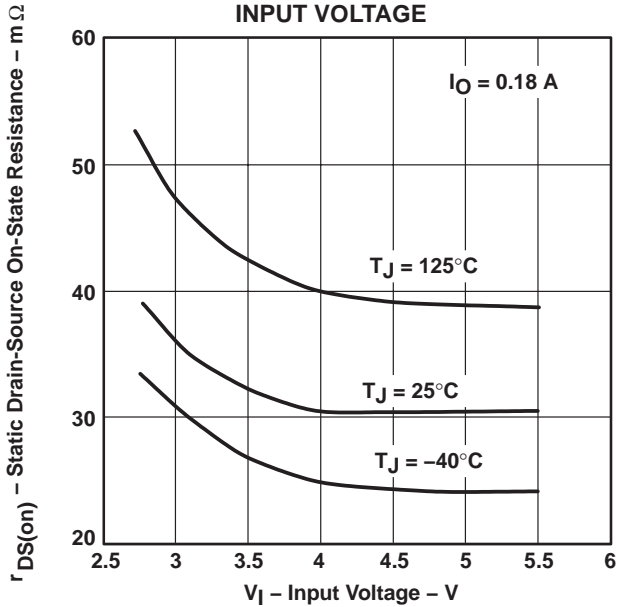


Figure 27

STATIC DRAIN-SOURCE ON-STATE RESISTANCE
vs
JUNCTION TEMPERATURE

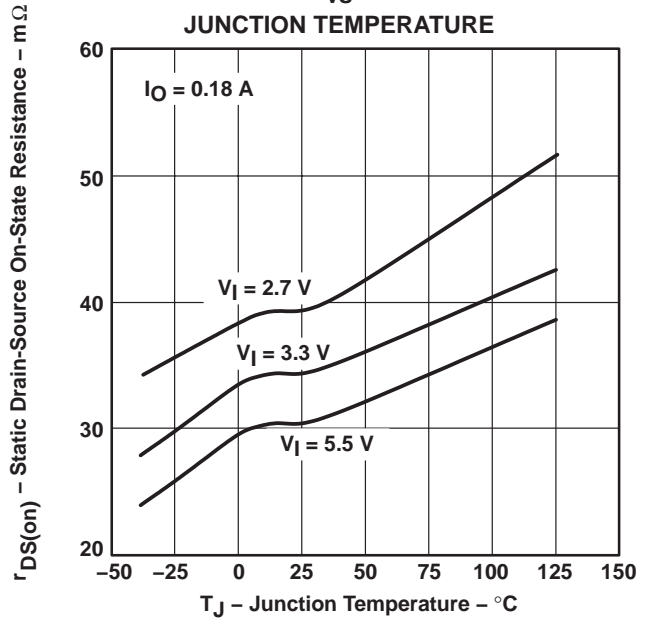


Figure 28

STATIC DRAIN-SOURCE ON-STATE RESISTANCE
vs
INPUT VOLTAGE

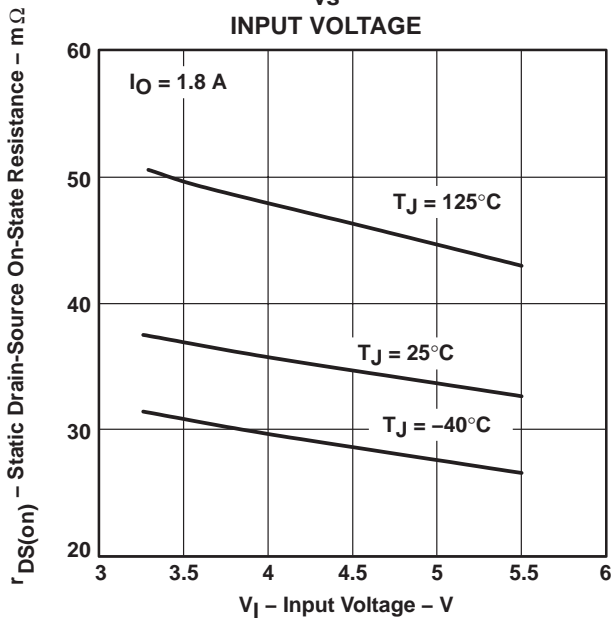


Figure 29

STATIC DRAIN-SOURCE ON-STATE RESISTANCE
vs
JUNCTION TEMPERATURE

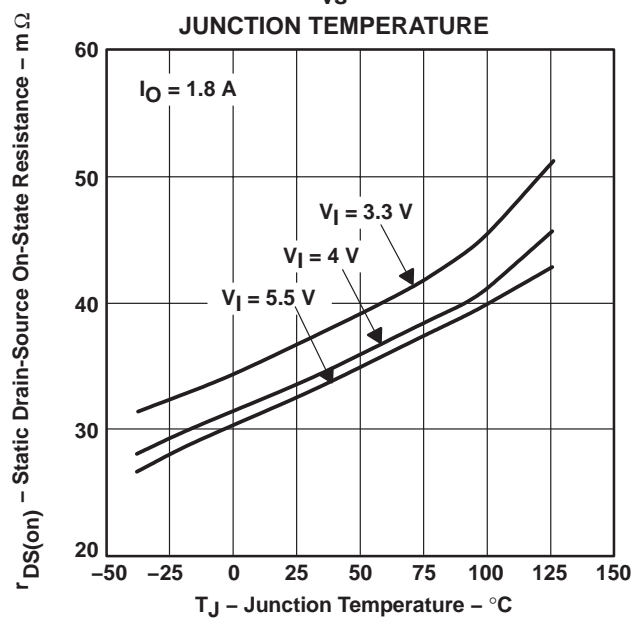


Figure 30

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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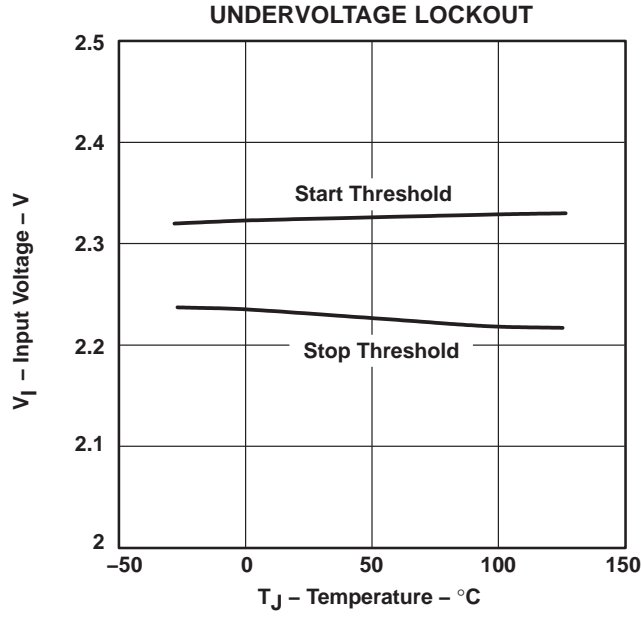


Figure 31

APPLICATION INFORMATION

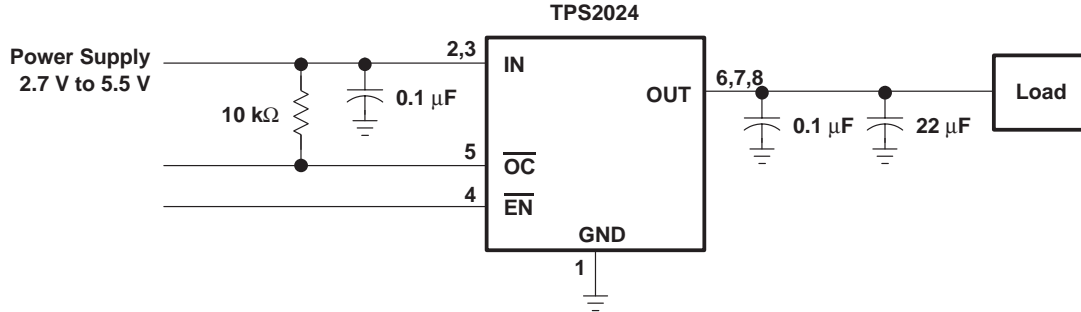


Figure 32. Typical Application

power-supply considerations

A 0.01- μF to 0.1- μF ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the output and input pins is recommended when the output load is heavy. This precaution reduces power supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01- μF to 0.1- μF ceramic capacitor improves the immunity of the device to short-circuit transients.

overcurrent

A sense FET checks for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before $V_{I(IN)}$ has been applied (see Figure 6). The TPS202x senses the short and immediately switches into a constant-current output.

In the second condition, the excessive load occurs while the device is enabled. At the instant the excessive load occurs, high currents may flow for a short time before the current-limit circuit can react (see Figure 11 through Figure 16). After the current-limit circuit has tripped (reached the overcurrent trip threshold) the device switches into constant-current mode.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached or until the thermal limit of the device is exceeded (see Figure 7 through Figure 9). The TPS202x is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its constant-current mode.

$\overline{\text{OC}}$ response

The $\overline{\text{OC}}$ open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output remains asserted until the overcurrent or overtemperature condition is removed. Connecting a heavy capacitive load to an enabled device can cause momentary false overcurrent reporting from the inrush current flowing through the device, charging the downstream capacitor. An RC filter can be connected to the $\overline{\text{OC}}$ pin to reduce false overcurrent reporting. Using low-ESR electrolytic capacitors on the output lowers the inrush current flow through the device during hot-plug events by providing a low-impedance energy source, thereby reducing erroneous overcurrent reporting.

TPS2021-Q1, TPS2022-Q1, TPS2024-Q1 POWER-DISTRIBUTION SWITCHES

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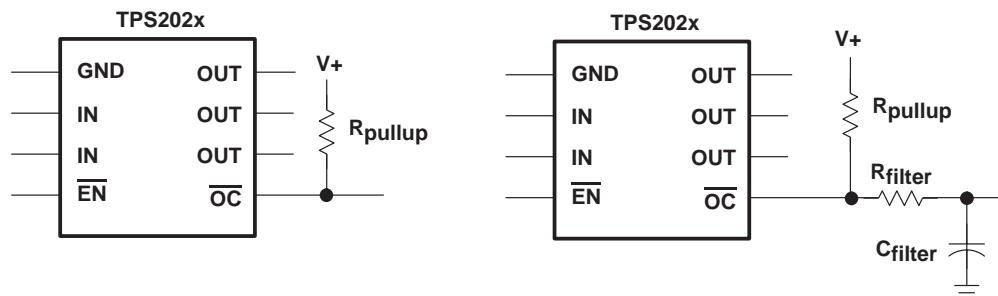


Figure 33. Typical Circuit for $\overline{\text{OC}}$ Pin and RC Filter for Damping Inrush $\overline{\text{OC}}$ Responses

power dissipation and junction temperature

The low on-resistance on the n-channel MOSFET allows small surface-mount packages, such as SOIC, to pass large currents. The thermal resistances of these packages are high compared to those of power packages; it is good design practice to check power dissipation and junction temperature. The first step is to find $r_{\text{DS(on)}}$ at the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and read $r_{\text{DS(on)}}$ from Figure 27 through Figure 30. Next, calculate the power dissipation using:

$$P_D = r_{\text{DS(on)}} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta\text{JA}} + T_A$$

Where:

T_A = Ambient temperature ($^{\circ}\text{C}$)

$R_{\theta\text{JA}}$ = Thermal resistance SOIC = $172^{\circ}\text{C}/\text{W}$

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation, using the calculated value as the new estimate. Two or three iterations are generally sufficient to get an acceptable answer.

thermal protection

Thermal protection prevents damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The faults force the TPS202x into constant current mode, which causes the voltage across the high-side switch to increase; under short-circuit conditions, the voltage across the switch is equal to the input voltage. The increased dissipation causes the junction temperature to rise to high levels. The protection circuit senses the junction temperature of the switch and shuts it off. Hysteresis is built into the thermal sense circuit and after the device has cooled approximately 20 degrees, the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed.

undervoltage lockout (UVLO)

A UVLO ensures that the power switch is in the off state at power-up. When the input voltage falls below approximately 2 V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems in which it is not possible to turn off the power switch before input power is removed. The UVLO also keeps the switch from being turned on until the power supply has reached at least 2 V, even if the switch is enabled. Upon reinsertion, the power switch is turned on, with a controlled rise time to reduce EMI and voltage overshoots.

generic hot-plug applications

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications (see Figure 34). Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Because of the controlled rise times and fall times of the TPS202x series, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the TPS202x also ensures the switch is off after the card has been removed, and the switch is off during the next insertion. The UVLO feature assures a soft start with a controlled rise time for every insertion of the card or module.

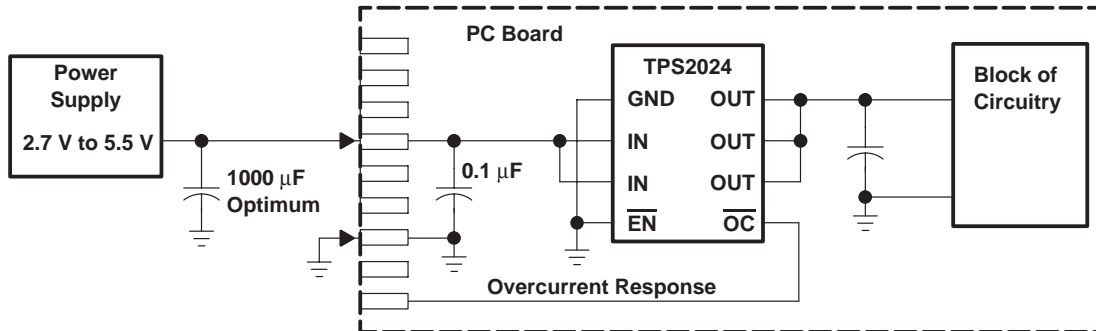


Figure 34. Typical Hot-Plug Implementation

By placing the TPS202x between the V_{CC} input and the rest of the circuitry, the input power reaches this device first after insertion. The typical rise time of the switch is approximately 9 ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge currents and provides a hot-plugging mechanism for any device.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS2021IDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2022DRG4Q1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2022DRQ1	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
TPS2024IDRG4Q1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2024IDRQ1	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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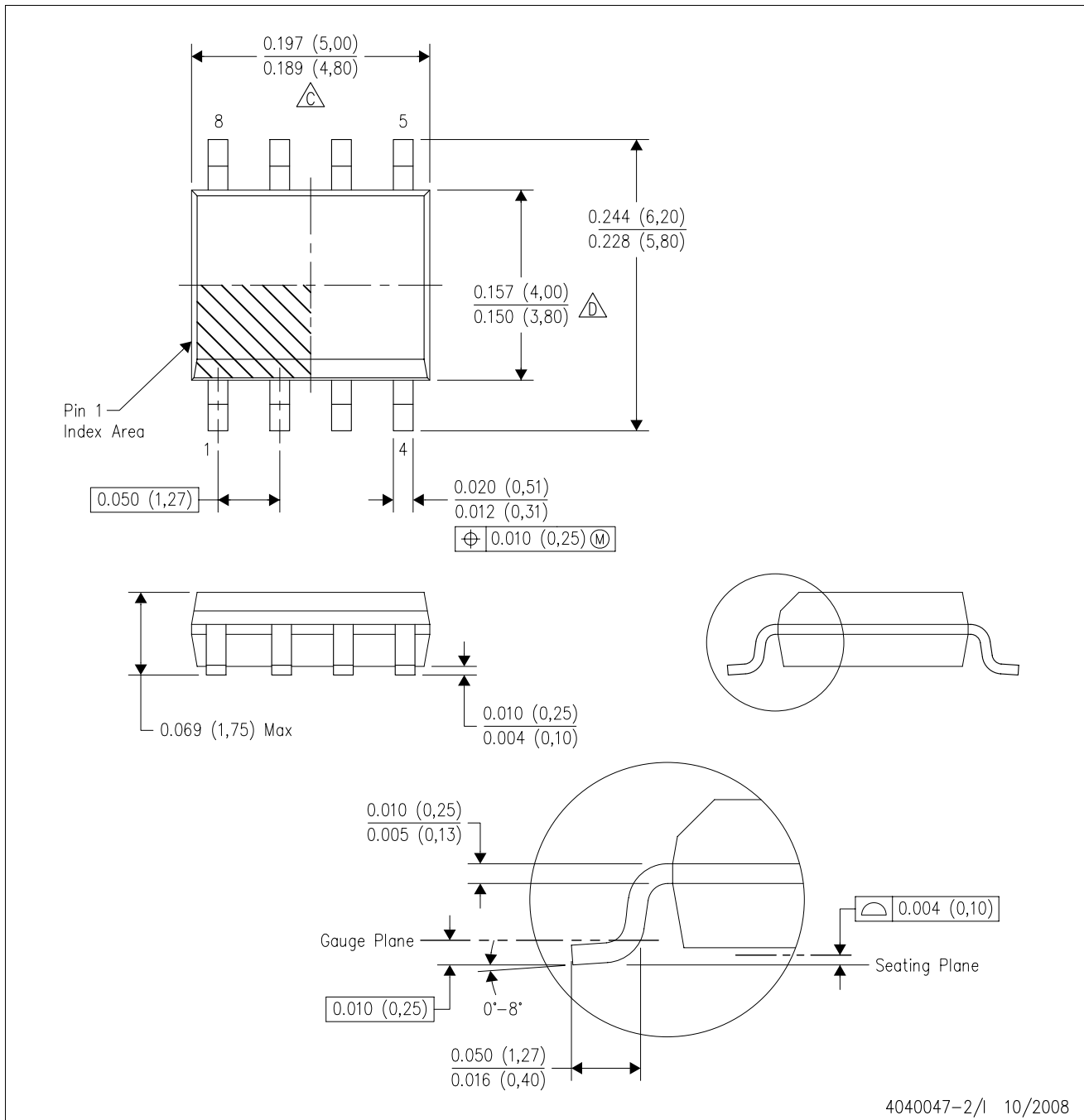
- Catalog: [TPS2021](#), [TPS2022](#), [TPS2024](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
 - E. Reference JEDEC MS-012 variation AA.

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